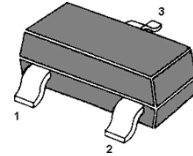


MMBTSA1182 PNP Silicon Epitaxial Planar Transistor

for low frequency power amplifier applications

The transistor is subdivided into two groups, O and Y according to its DC current gain.



1.Base 2.Emitter 3.Collector
SOT-23 Plastic Package

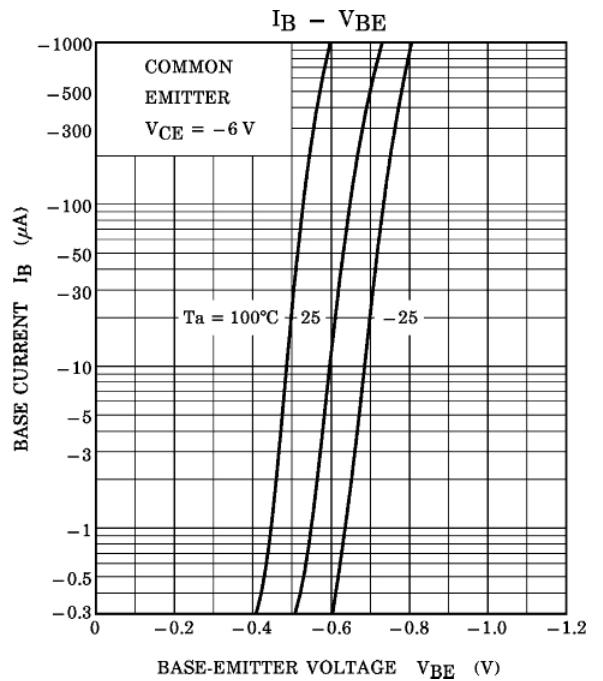
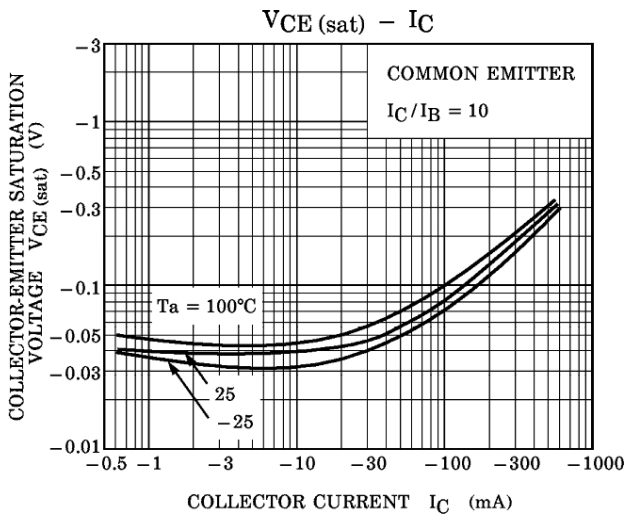
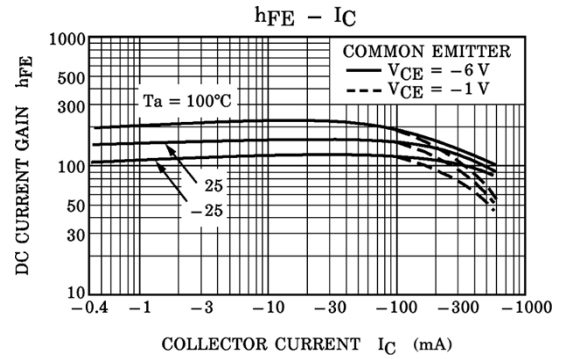
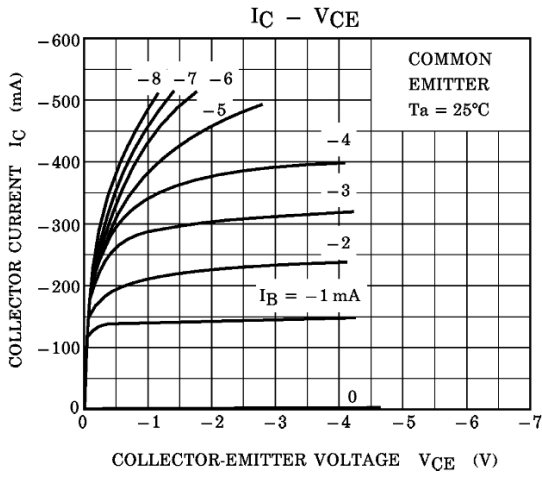
Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	35	V
Collector Emitter Voltage	$-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	500	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_s	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	O	h_{FE}	70	-	140	-
	Y	h_{FE}	120	-	240	-
		h_{FE}	25	-	-	-
Collector Cutoff Current at $-V_{CB} = 35\text{ V}$	$-I_{CBO}$	-	-	0.1	μA	
Emitter Cutoff Current at $-V_{EB} = 5\text{ V}$	$-I_{EBO}$	-	-	0.1	μA	
Collector Emitter Saturation Voltage at $-I_C = 100\text{ mA}$, $-I_B = 10\text{ mA}$	$-V_{CE(sat)}$	-	-	0.25	V	
Base Emitter On Voltage at $-V_{CE} = 1\text{ V}$, $-I_C = 100\text{ mA}$	$-V_{BE(on)}$	-	-	1	V	
Transition Frequency at $-V_{CE} = 6\text{ V}$, $-I_C = 20\text{ mA}$	f_T	-	200	-	MHz	
Collector Output Capacitance at $-V_{CB} = 6\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	13	-	pF	

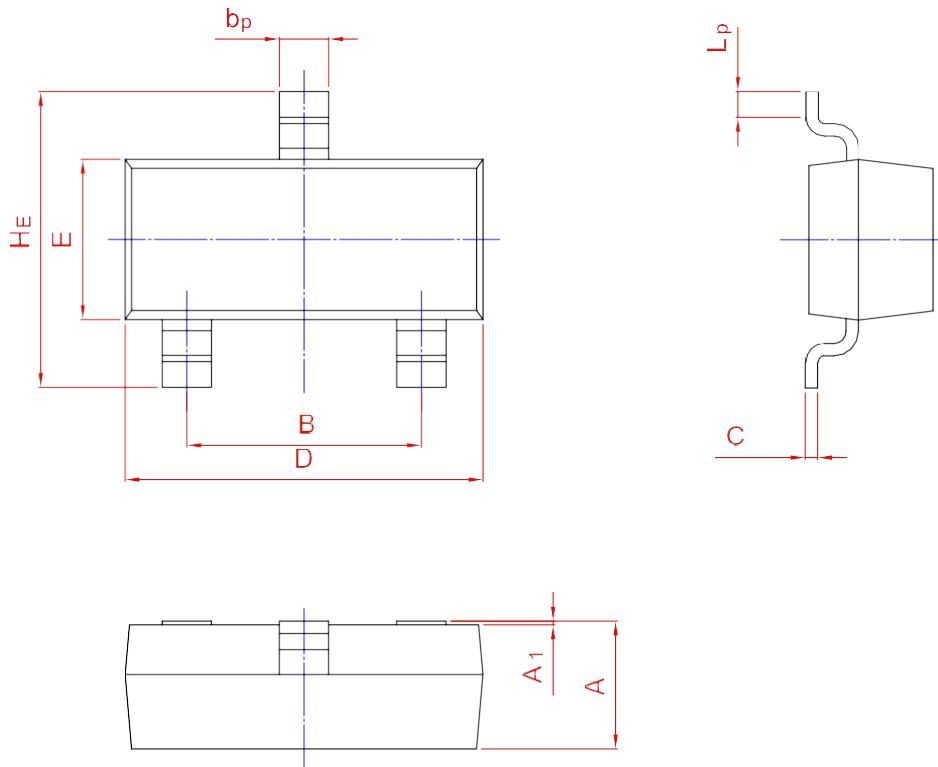
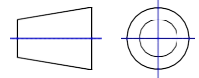
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b _p	C	D	E	H _E	A ₁	L _p
mm	1.40	2.04	0.50	0.19	3.10	1.65	3.00	0.100	0.50
	0.95	1.78	0.35	0.08	2.70	1.20	2.20	0.013	0.20